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WHAT IS CLAIMED IS:

1. A method of preparing porous materials,  
comprising the steps of:

(A) making a solution containing silicon and  
surfactant be in contact with a substrate having  
alignment control ability; and

(B) drying said substrate made in contact  
with the solution to remove the solvents  
contained in said solution.

2. A method according to claim 1, wherein  
silicon is contained in said solution in a state  
of compound.

3. A method according to claim 1 or 2,  
wherein silicon is contained in said solution as  
silicon alkoxides.

4. A method of preparing porous materials,  
comprising the steps of:  
coating a substrate having alignment control  
ability with a surfactant solution containing  
silicon alkoxide; and  
drying said substrate.

5. A method according to claim 4, wherein  
patterned mesostructured silica with uniaxially

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aligned channel structure is formed by a step of coating a desired position of a substrate having alignment control ability with a surfactant solution containing silicon alkoxide in a  
5 desired shape and a step of drying said substrate.

6. A method according to claim 4 or 5,  
wherein said substrate with alignment control  
10 ability is a silicon single crystal substrate having (110) orientation.

7. A method according to claim 4 or 5,  
wherein said substrate is a substrate whose  
15 surface is coated with a polymer compound film subjected to a rubbing process.

8. A method according to claim 4 or 5,  
wherein said substrate is a substrate whose  
20 surface is coated with a Langmuir-Blodgett film of polymer compound.

9. A method according to any one of claims  
4 to 8, wherein the substrate is coated with the  
25 surfactant solution by a pen lithography method.

10. A method according to any one of claims

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4 to 8, wherein the substrate is coated with the surfactant solution by an ink jet method.

11. A method according to any one of claims 4 to 8, wherein the substrate is coated with the surfactant solution by a dip coating method.

12. A method of preparing porous materials, comprising the steps of:

coating a substrate having alignment control ability with a solution of surfactant containing silicon alkoxides;

drying said substrate; and  
removing the surfactant.

13. A method according to claim 12, wherein said step of coating said substrate with said solution is a step of selectively coating a desired position of said substrate with said solution in a desired shape.

14. A method according to claim 12 or 13, wherein said substrate with alignment control ability is a silicon single crystal substrate having (110) orientation.

15. A method according to claim 12 or 13,

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10            17. A method according to any one of claims  
12 to 16, wherein said substrate is coated with  
said surfactant solution by a pen lithography  
method.

19. A method according to any one of claims  
20 12 to 16, wherein said substrate is coated with  
said surfactant solution by a dip coating method.

25 (A) attaching a solution containing silicon  
and surfactant to a substrate having alignment  
control ability; and

(B) removing the solvents contained in said solution attached to said substrate.

21. A method according to claim 20, wherein  
5 silicon is contained in said solution in the form of compound.

22. A method according to claim 20, wherein  
10 silicon is contained in said solution as silicon alkoxides.

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